# TER effect modulated by interface band profile engineering

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## Normal ferroelectric tunnel junction



$$w = \sqrt{\frac{2\varepsilon_0 \varepsilon_{\text{stat}} (V + V'_{bi})}{eN_{\text{eff}}}}$$

Barrier thickness ≤ 2w



Asymmetric screening charge will affect the band structure.

Zhuravlev, et. al. PRL 94, 246802 (2005)

### Normal ferroelectric tunnel junction



FE reversal changes screening charge type. Different transport mechanisms through a junction barrier.

Pantel, et. al. PRB 82, 134105 (2010)

Zhuravlev, et. al. PRL 94, 246802 (2005)

#### FTJ with different metal electrodes



Electrodes with different work functions. Negative bias favors FN tunneling.

Boyn, et. al. APL Mater. 3, 061101 (2015)

#### FTJ with different metal electrodes



Typical TER values vary from 200 for W to 20 000 for Ir. This variation is mainly due to the large increase of the OFF state resistance with the TE work function as the ON state resistance does not show a clear trend.

Boyn, et. al. APL Mater. 3, 061101 (2015)



Semiconducting electrode with FE controlled depletion layer.



d+wp

 $+\sigma_{D}=qN_{D}w_{D}$ 

x

x

EF

Ee

Wen, et. al. Nat. Mater. 12, 617 (2013)



Wen, et. al. Nat. Mater. 12, 617 (2013)

TER is enhanced by SE electrode.



Xi, et. al. Nat. Commun. 8, 15217 (2017)



#### Doping level in NSTO affects TER as well.

DT for 1wt% FTJ; TI for lightly doped FTJ at OFF state.



0.01

0.1

Nb concentration (wt%)

Xi, et. al. Nat. Commun. 8, 15217 (2017)

Capacitance measurement shows the structure of the band.



Xi, et. al. Nat. Commun. 8, 15217 (2017)